

High voltage discharge, High speed switching, Low Noise (–60V, –3A)

2SA2073

●Features

- 1) High speed switching. (t_f : Typ. : 20ns at $I_C = -3A$)
- 2) Low saturation voltage, typically.
(Typ. : $-200mV$ at $I_C = -2.0A$, $I_B = -200mA$)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Low Noise.
- 5) Complements the 2SC5826.

●Applications

High speed switching, Low noise

●Structure

PNP silicon epitaxial planar transistor

●Packaging specifications

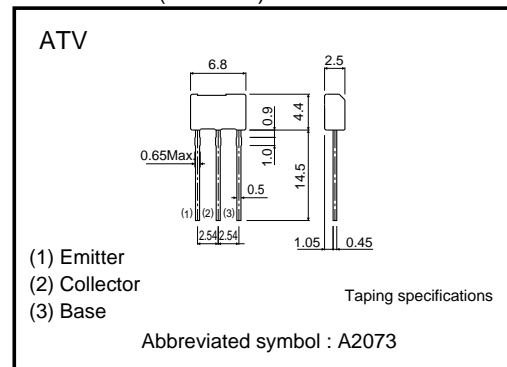
Type	Package	Taping
	Code	TV2
	Basic ordering unit (pieces)	2500
2SA2073		○

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CB0}	–60	V	
Collector-emitter voltage	V_{CE0}	–60	V	
Emitter-base voltage	V_{EB0}	–6	V	
Collector current	DC	I_C	–3	A
	Pulsed	I_{CP}	–6	A *
Power dissipation	P_C	1.0	W	
Junction temperature	T_J	150	°C	
Range of storage temperature	T_{stg}	–55 to 150	°C	

*Pw=10ms

●Dimensions (Unit : mm)



Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	BV_{CEO}	-60	-	-	V	$I_C = -1\text{mA}$
Collector-base breakdown voltage	BV_{CBO}	-60	-	-	V	$I_C = -100\mu\text{A}$
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	$I_E = -100\mu\text{A}$
Collector cut-off current	I_{CBO}	-	-	-1.0	μA	$V_{CB} = -40\text{V}$
Emitter cut-off current	I_{EBO}	-	-	-1.0	μA	$V_{EB} = -4\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-200	-500	mV	$I_C = -2.0\text{A}$ $I_B = -200\text{mA}$
DC current gain	h_{FE}	120	-	270	-	$V_{CE} = -2\text{V}$ $I_C = -100\text{mA}$
Transistor frequency	f_T	-	200	-	MHz	$V_{CE} = -10\text{V}$ $I_E = 100\text{mA}$ $f = 10\text{MHz}$
Collector output capacitance	C_{ob}	-	40	-	pF	$V_{CB} = -10\text{V}$ $I_E = 0\text{mA}$ $f = 1\text{MHz}$
Turn-on time	t_{on}	-	20	-	ns	$I_C = -3\text{A}$ $I_{B1} = -300\text{mA}$
Storage time	t_{stg}	-	130	-	ns	$I_{B2} = 300\text{mA}$
Fall time	t_f	-	20	-	ns	$V_{CC} = -25\text{V}$

*1 Single pulse

*2 See switching characteristics measurement circuits

● h_{FE} RANK

Q
120-270

Transistors

●Electrical characteristics curves

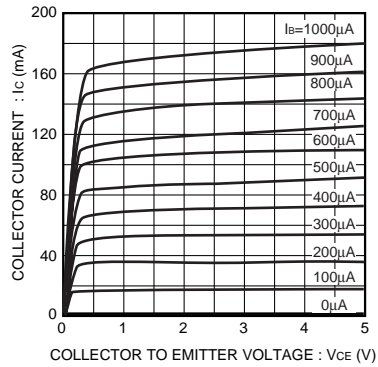


Fig.1 Typical output characteristics

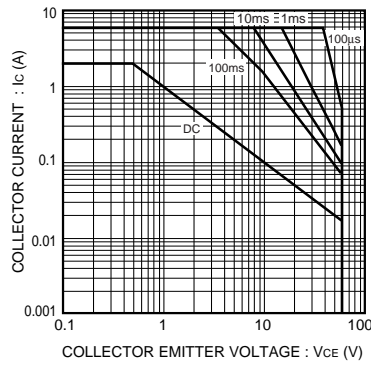


Fig.2 Safe operating area

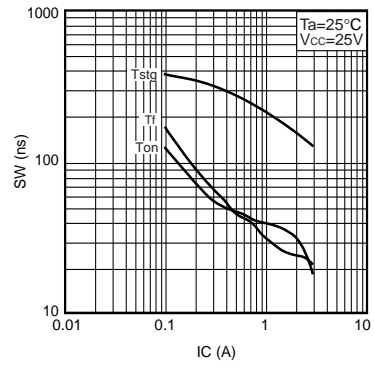


Fig.3 Switching Time

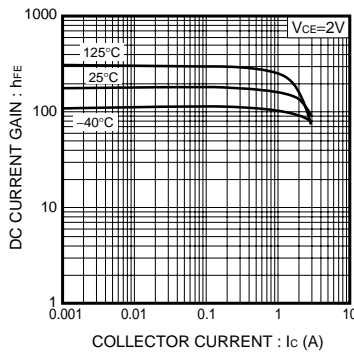


Fig.4 DC current gain vs. collector current (I)

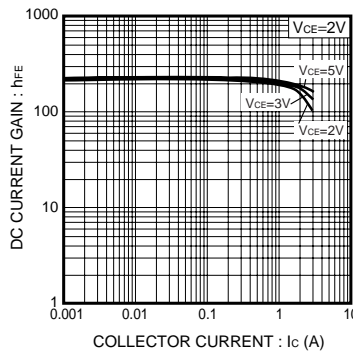


Fig.5 DC current gain vs. collector current (II)

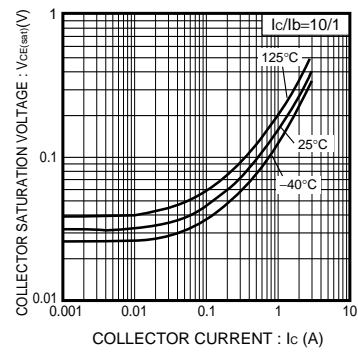


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

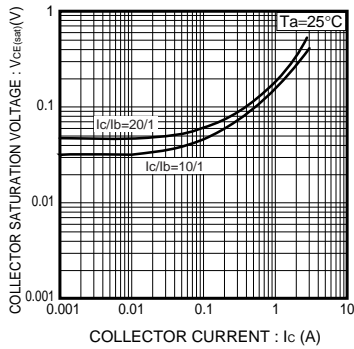


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

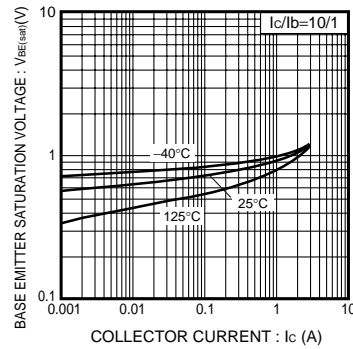


Fig.8 Base-emitter saturation voltage vs. collector current

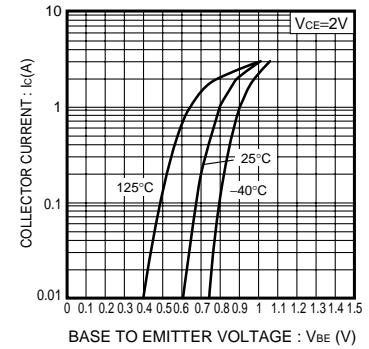


Fig.9 Grounded emitter propagation characteristics

Transistors

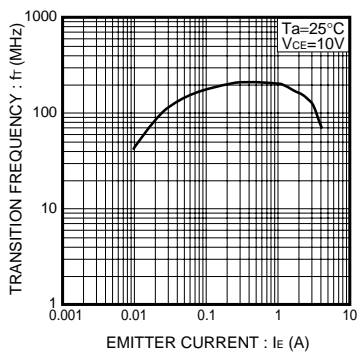


Fig.10 Transition frequency

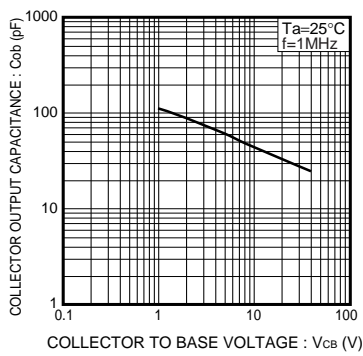
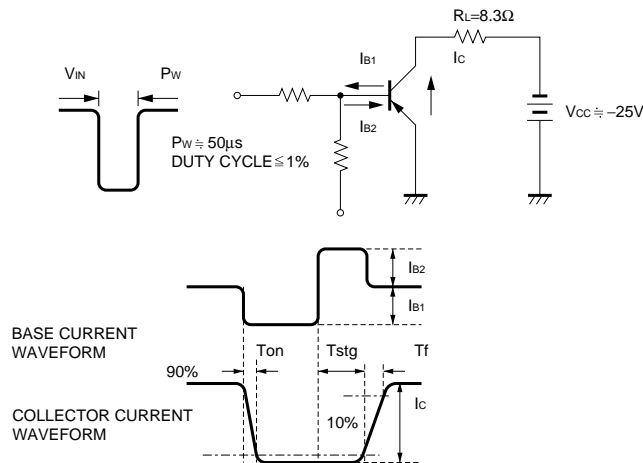


Fig.11 Collector output capacitance

●Switching characteristics measurement circuits



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